



N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

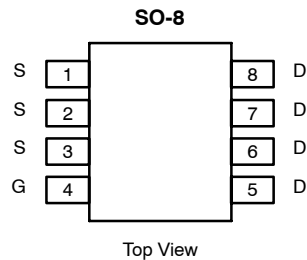
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0135 @ $V_{GS} = 10$ V	10
	0.020 @ $V_{GS} = 4.5$ V	8

FEATURES

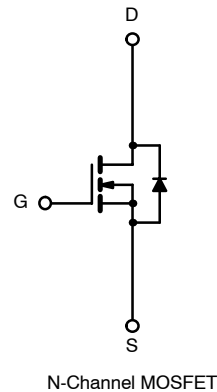
- TrenchFET® Power MOSFET
- 100% R_g Tested

APPLICATIONS

- Battery Switch



Ordering Information: Si4410BDY
Si4410BDY-T1 (with Tape and Reel)



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	10	7.5	A
	T _A = 70°C		8	6	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	50		
Continuous Source Current (Diode Conduction) ^a		I _S	2.3	1.26	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	2.5	1.4	W
	T _A = 70°C		1.6	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	40	50	$^\circ\text{C/W}$
	Steady State		70	90	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	30	

Notes

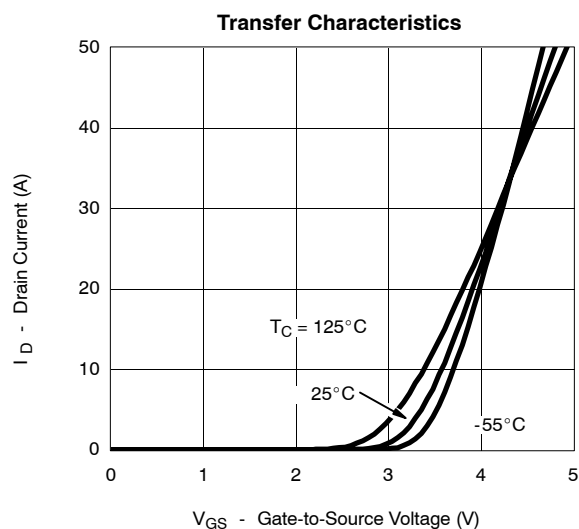
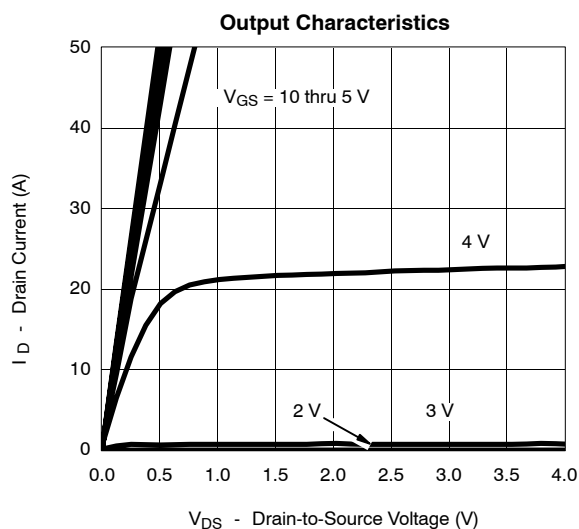
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$		0.011	0.0135	Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 5\ \text{A}$		0.0165	0.020	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 10\ \text{A}$		25		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.76	1.1	V
Dynamic^b						
Gate Charge	Q_g	$V_{DS} = 15\ \text{V}$, $V_{GS} = 5\ \text{V}$, $I_D = 10\ \text{A}$		13	20	nC
Total Gate Charge	Q_{gt}	$V_{DS} = 15\ \text{V}$, $V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$		25	40	
Gate-Source Charge	Q_{gs}			5.5		
Gate-Drain Charge	Q_{gd}			3.7		
Gate Resistance	R_g	$f = 1\ \text{MHz}$	0.5	1.6	2.7	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 25\ \text{V}$, $R_L = 25\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_G = 6\ \Omega$		10	15	ns
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			40	60	
Fall Time	t_f			15	25	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.3\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		35	70	

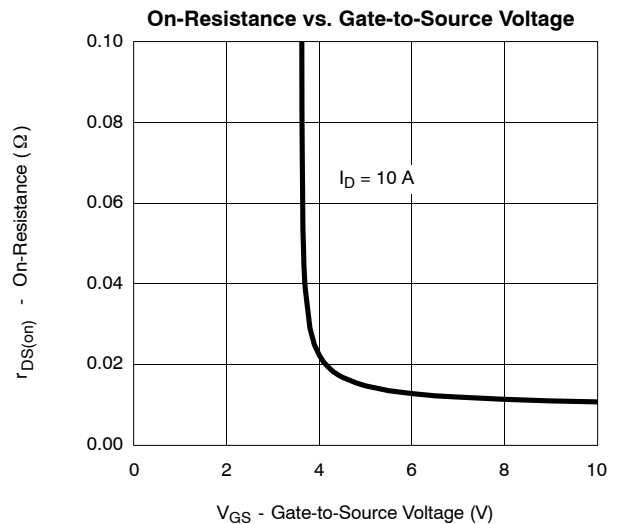
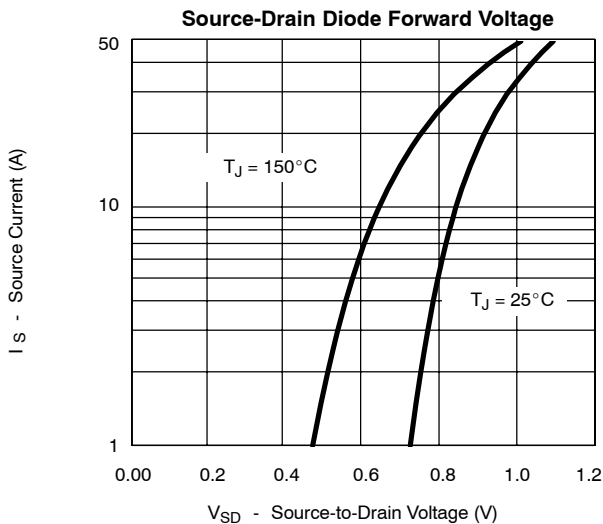
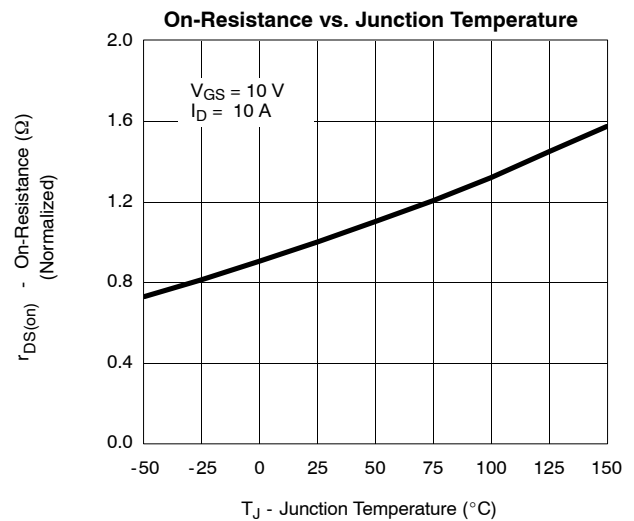
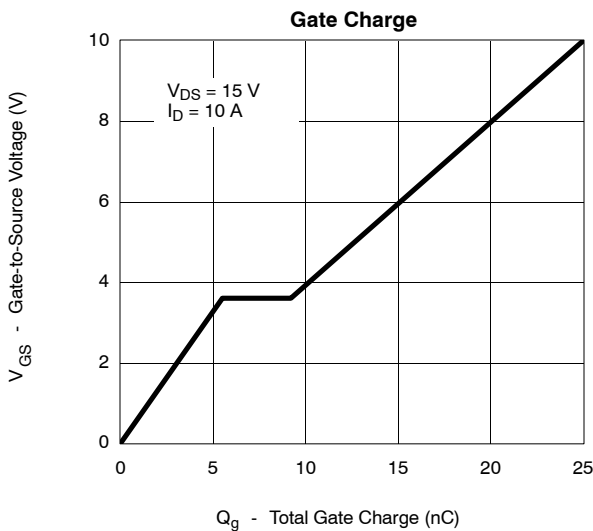
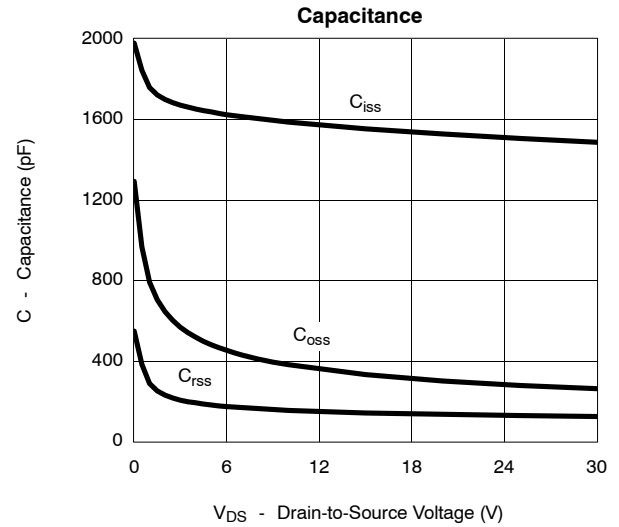
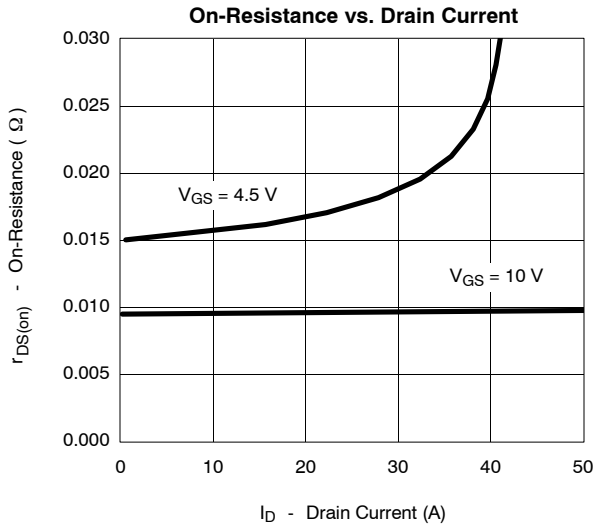
Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

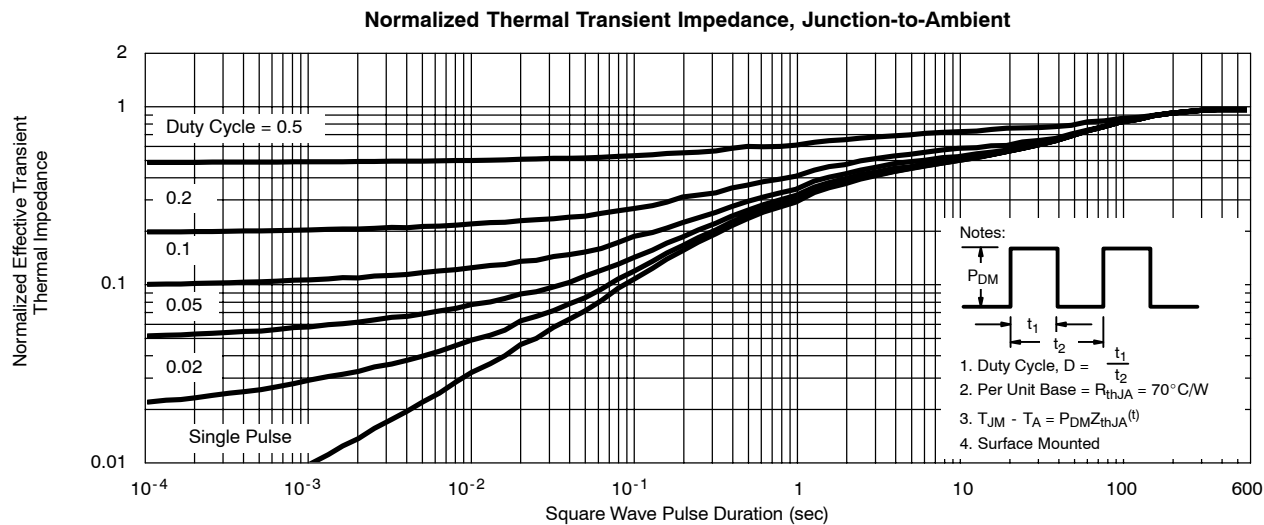
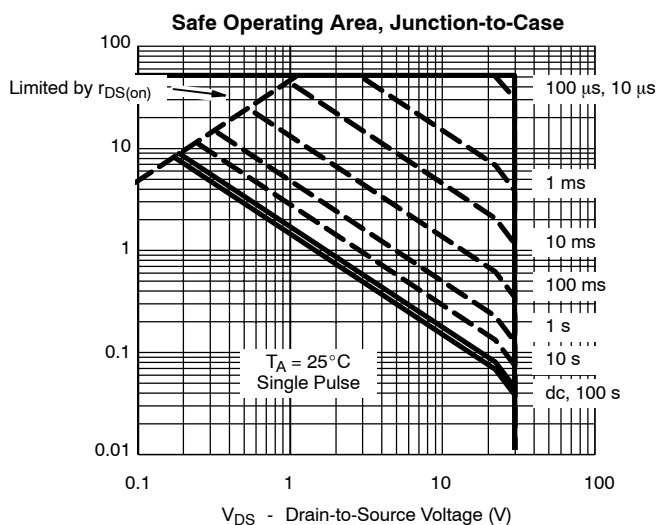
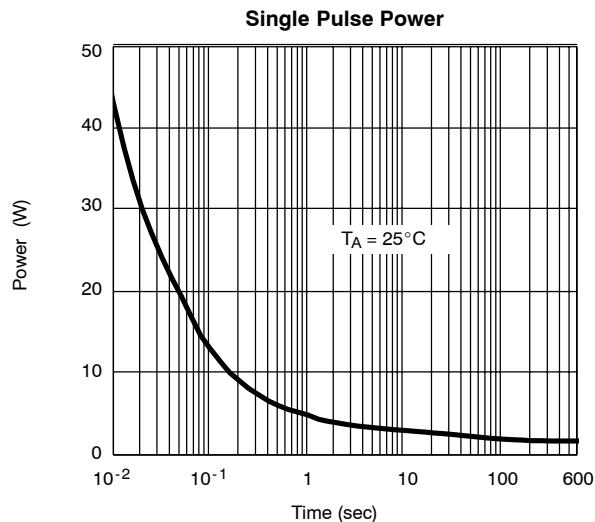
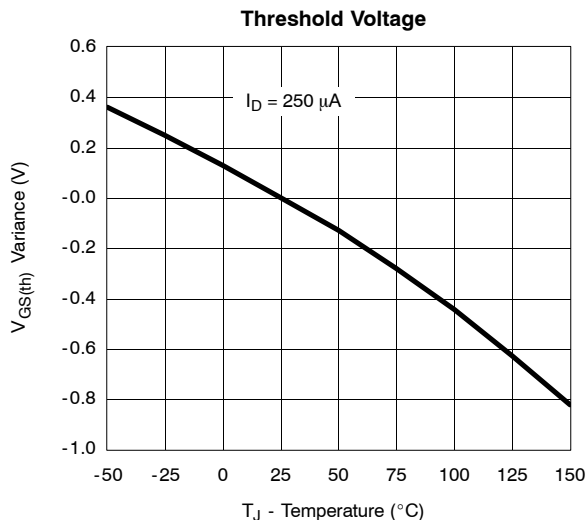
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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